

CLAIMS:

1. A semiconductor component comprising at least one lateral bipolar power transistor which is composed of at least one group of single transistors with a common collector-, base- and emitter zone, which are parallel connected by three conductor track systems which bring together the emitter-, base- and collector currents of each of the single transistors; and each single transistor comprises an emitter region having an emitter-contact zone with an emitter contact, at least one active emitter zone and a connection zone between the contact zone and the active zone, a base region having a base-contact zone with a base contact and an internal base series resistor, and a collector region, characterized in that said internal base series resistor is a structured semiconductor region comprised of at least two ring segments, which is connected to the base-contact zone and the base contact.
2. A semiconductor component as claimed in claim 1, characterized in that the internal base series resistor is a structured semiconductor region with emitter doping.
3. A semiconductor component as claimed in claim 1, characterized in that the overlay region between the base conductor track system and the base series resistor is minimized.
4. A semiconductor component as claimed in claim 1, characterized in that the conductor track systems are formed by a single layer metallization.